Erratum: Room-Temperature Ferromagnetism in Mn-Doped Semiconducting $CdGeP_2$ [Phys. Rev. Lett. 88, 047205 (2002)]

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Figures 1 and 2 of our Letter contained errors in the allowed chemical potentials range. We have fixed these errors in the figures given below. The allowed formation energies are now evaluated using $\mu_{\mathrm{Cd}} + \mu_{\mathrm{Ge}} + 2\mu_P = \Delta H_f(\mathrm{CdGeP_2})$ (not $\leq$) and $\mu_{\mathrm{Mn}} + \mu_P \leq \Delta H_f(\mathrm{MnP})$ in addition to the conditions used in our paper. We use the experimental value of $\Delta H_f(\mathrm{MnP}) = -1$ eV. Further, the chemical potentials used in Fig. 3 should read "P-poor." The new results do not change the conclusions of our earlier work.

We thank S. H. Wei for pointing out some of the errors to us.

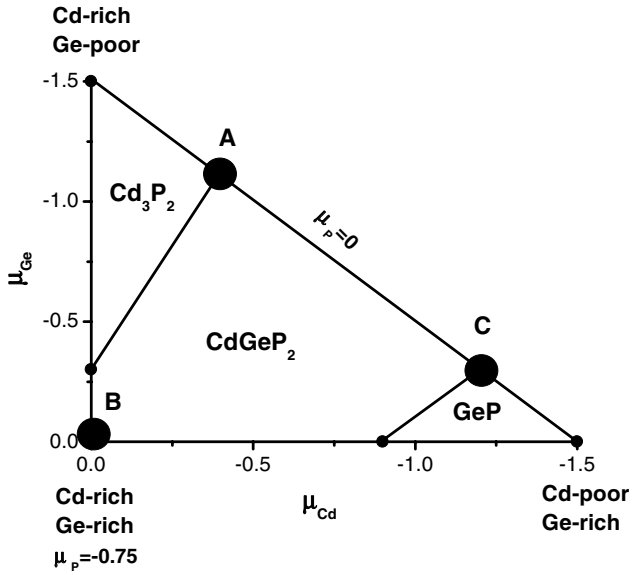

FIG. 1. The range of Cd and Ge chemical potentials where $CdGeP_2$, GeP, and Cd_3P_2 are stable. Note: $CdGeP_2$ has a single region of stability now.

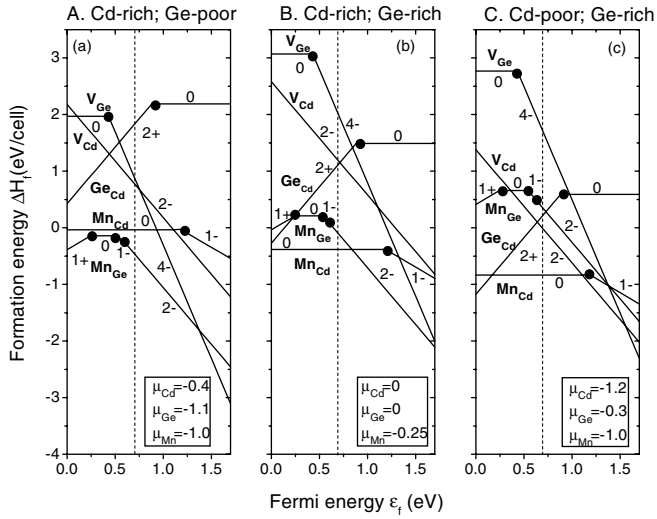

FIG. 2. The calculated formation energies as a function of Fermi energy for different charge states of isolated defects in a 64 atom cell of $CdGeP_2$ for chemical potentials: *A*, *B*, and *C*. The vertical dashed line (solid circle) denotes the calculated band gap (transition energy between charge states). Note: Now the defects V_{Ge}^{4-} [chemical potentials *A* and *C*, Fermi energy near the conduction band minimum (CBM)], V_{Cd}^{2-} (chemical potential *C*, Fermi energy near CBM), and Ge_{Cd}^{2+} [chemical potential *C*, Fermi energy near valence band maximum (VBM)] can be stabilized under chemical potentials and Fermi energies indicated in parentheses.

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